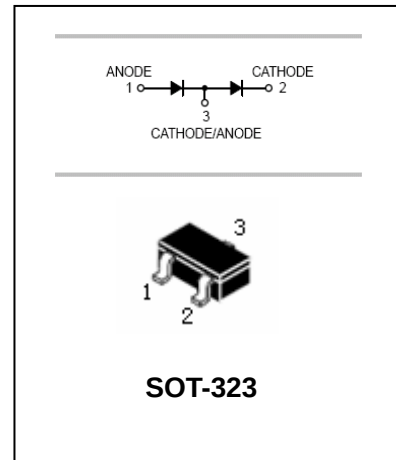


Schottky Barrier Diode

MMBD352W

FEATURES

- Very low capacitance-less than 1.0Pf
@zero volts.
- Low forward voltage-0.5 Voltage(Typ.)
@I_F=10mA.



APPLICATIONS

- For UHF mixer applications.

ORDERING INFORMATION

Type No.	Marking	Package Code
MMBD352W	M5	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Continuous reverse voltage	V _R	7.0	V
Power Dissipation	P _d	200	mW
Thermal resistance junction-to-ambient	R _{θJA}	625	
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55-+150	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	Typ.	MAX	UNIT
Reverse current	I _R	V _R =3.0V. V _R =7.0V			0.25 10	μA
Forward voltage	V _F	I _F =10mA			0.60	V
Diode capacitance	C _D	V _R =0V, f=1MHz			1.0	pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Schottky Barrier Diode

MMBD352W

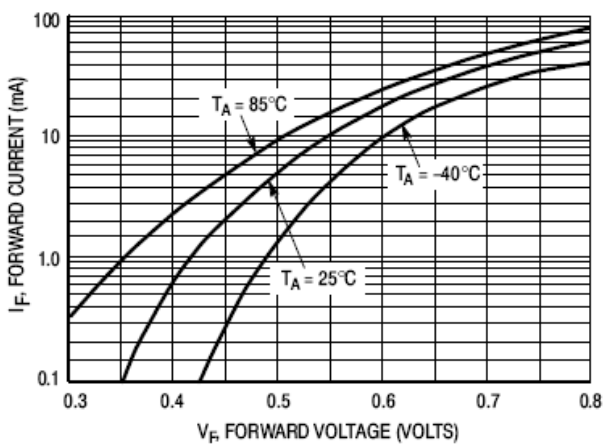


Figure 1. Forward Voltage

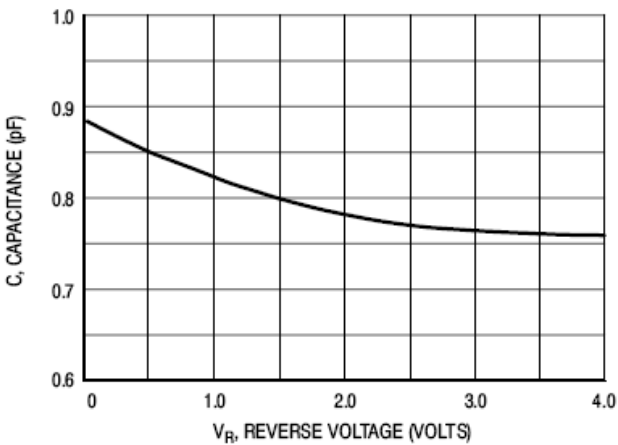
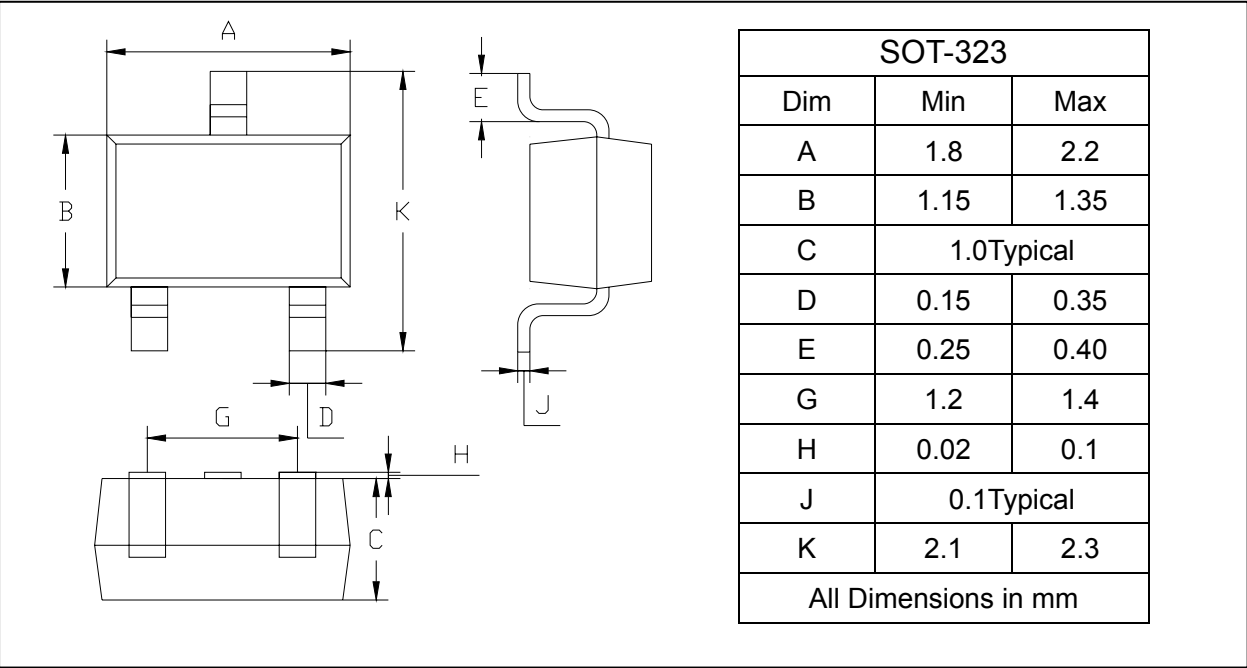


Figure 2. Capacitance

PACKAGE OUTLINE

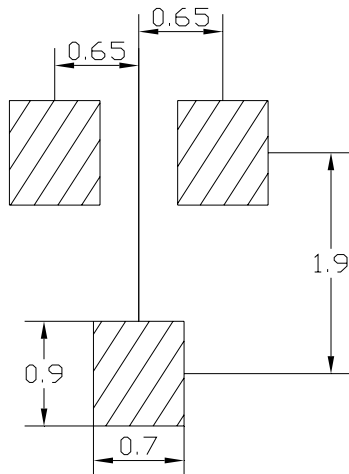
Plastic surface mounted package

SOT-323



Schottky Barrier Diode

MMBD352W

SOLDERING FOOTPRINT

Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
MMBD352W	SOT-323	3000/Tape&Reel